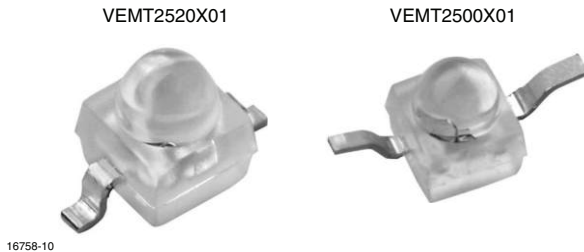


Silicon NPN Phototransistor



DESCRIPTION

VENT2500X01 series are silicon NPN epitaxial planar phototransistors in a miniature dome lens, clear epoxy package for surface mounting. The device is sensitive to visible and near infrared radiation.

FEATURES

- Package type: surface mount
- Package form: GW, RGW
- Dimensions (L x W x H in mm): 2.3 x 2.3 x 2.8
- AEC-Q101 qualified
- High radiant sensitivity
- Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 15^\circ$
- Package matched with IR emitter series VSMB2000X01
- Floor life: 4 weeks, MSL 2a, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition
- Find out more about Vishay's Automotive Grade Product requirements at: www.vishay.com/applications



APPLICATIONS

- Detector in automotive applications
- Photo interrupters
- Miniature switches
- Counters
- Encoders
- Position sensors

| PRODUCT SUMMARY | | | |
|-----------------|---------------|-----------------|----------------------|
| COMPONENT | I_{ca} (mA) | φ (deg) | $\lambda_{0.1}$ (nm) |
| VENT2500X01 | 6 | ± 15 | 470 to 1090 |
| VENT2520X01 | 6 | ± 15 | 470 to 1090 |

Note

Test condition see table "Basic Characteristics"

| ORDERING INFORMATION | | | |
|----------------------|---------------|------------------------------|------------------|
| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM |
| VENT2500X01 | Tape and reel | MOQ: 6000 pcs, 6000 pcs/reel | Reverse gullwing |
| VENT2520X01 | Tape and reel | MOQ: 6000 pcs, 6000 pcs/reel | Gullwing |

Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS | | | | |
|---------------------------|---------------------------|-----------|-------|------|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
| Collector emitter voltage | | V_{CEO} | 20 | V |
| Emitter collector voltage | | V_{ECO} | 7 | V |
| Collector current | | I_C | 50 | mA |
| Power power dissipation | $T_{amb} \leq 75^\circ C$ | P_V | 100 | mW |



| ABSOLUTE MAXIMUM RATINGS | | | | |
|-------------------------------------|----------------------------|-------------------|---------------|--------------------|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
| Junction temperature | | T_j | 100 | $^{\circ}\text{C}$ |
| Operating temperature range | | T_{amb} | - 40 to + 100 | $^{\circ}\text{C}$ |
| Storage temperature range | | T_{stg} | - 40 to + 100 | $^{\circ}\text{C}$ |
| Soldering temperature | Acc. reflow profile fig. 7 | T_{sd} | 260 | $^{\circ}\text{C}$ |
| Thermal resistance junction/ambient | Acc. J-STD-051 | R_{thJA} | 250 | K/W |

Note

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified

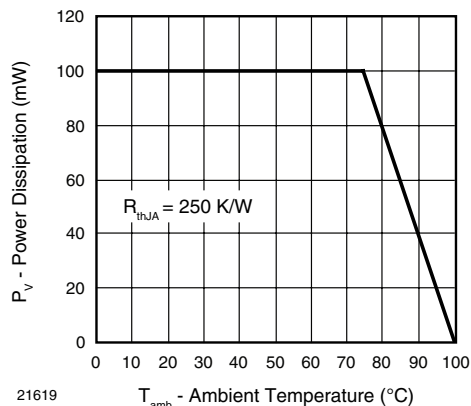


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS | | | | | | |
|--------------------------------------|---|--------------------|------|-------------|------|------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Collector emitter breakdown voltage | $I_C = 0.1\text{ mA}$ | V_{CEO} | 20 | | | V |
| Collector dark current | $V_{\text{CE}} = 5\text{ V}, E = 0$ | I_{CEO} | | 1 | 100 | nA |
| Collector emitter capacitance | $V_{\text{CE}} = 0\text{ V}, f = 1\text{ MHz}, E = 0$ | C_{CEO} | | 25 | | pF |
| Collector light current | $E_e = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}, V_{\text{CE}} = 5\text{ V}$ | I_{CA} | 3 | 6 | 9 | mA |
| Angle of half sensitivity | | ϕ | | ± 15 | | deg |
| Wavelength of peak sensitivity | | λ_p | | 850 | | nm |
| Range of spectral bandwidth | | $\lambda_{0.1}$ | | 470 to 1090 | | nm |
| Collector emitter saturation voltage | $I_C = 0.05\text{ mA}$ | V_{CEsat} | | | 0.4 | V |

Note

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

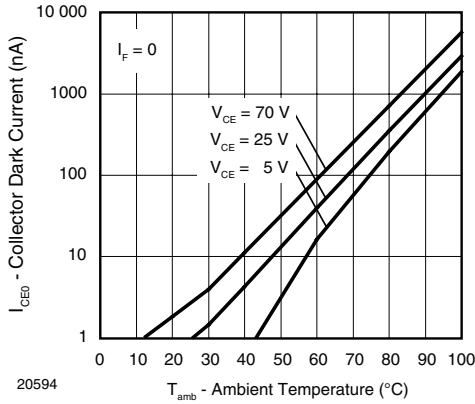


Fig. 2 - Collector Dark Current vs. Ambient Temperature

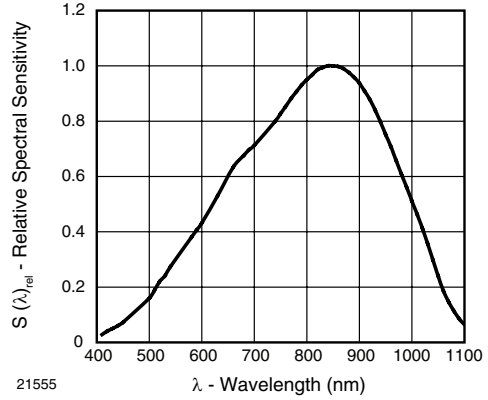


Fig. 5 - Relative Spectral Sensitivity vs. Wavelength

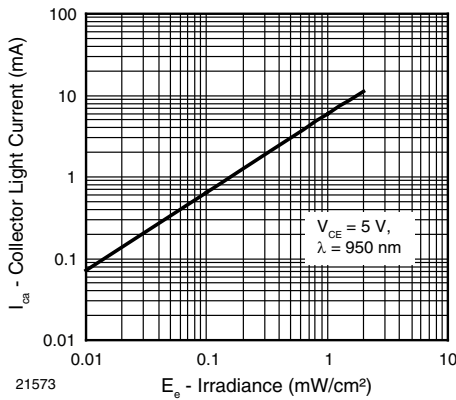


Fig. 3 - Collector Light Current vs. Irradiance

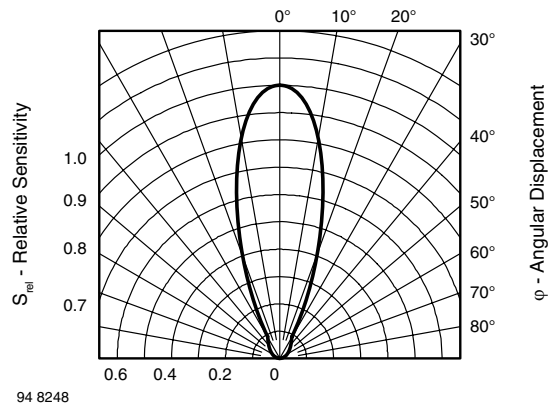


Fig. 6 - Relative Radiant Sensitivity vs. Angular Displacement

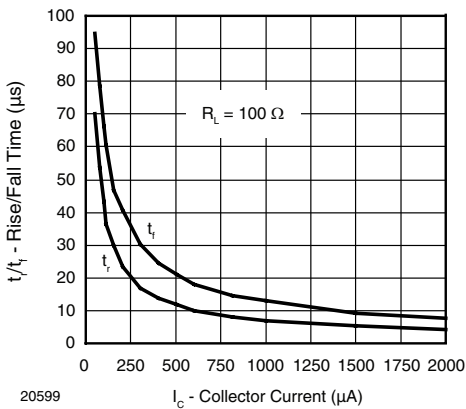


Fig. 4 - Rise/Fall Time vs. Collector Current

REFLOW SOLDER PROFILE

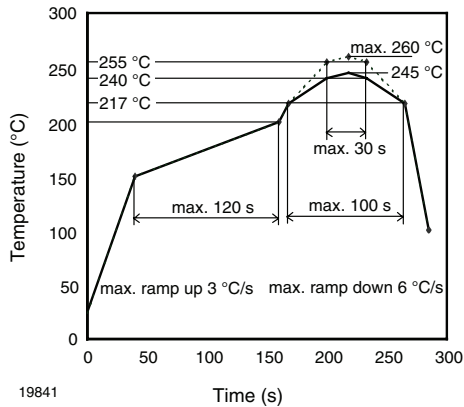


Fig. 7 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 4 weeks

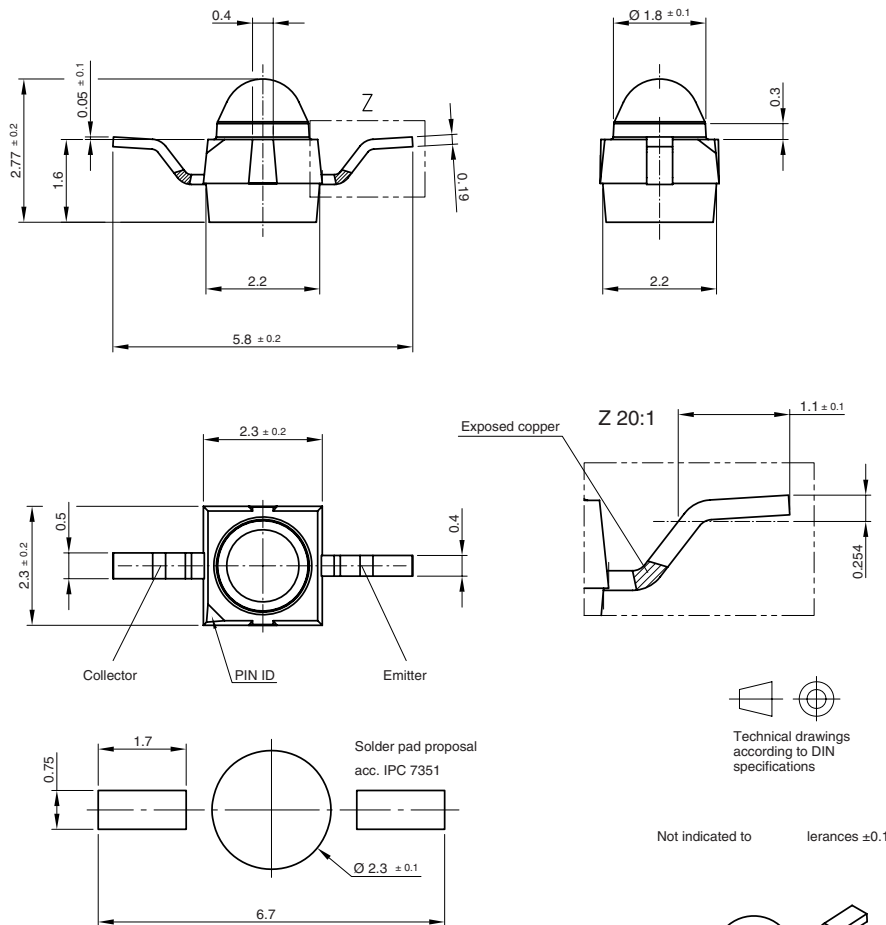
Conditions: $T_{amb} < 30\text{ °C}$, $RH < 60\%$

Moisture sensitivity level 2a, acc. to J-STD-020.

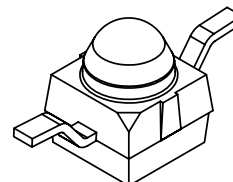
DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C), $RH < 5\%$.

PACKAGE DIMENSIONS VENT2500X01 in millimeters



Drawing-No.: 6.544-5391.01-4
Issue: 1; 26.09.08
21570



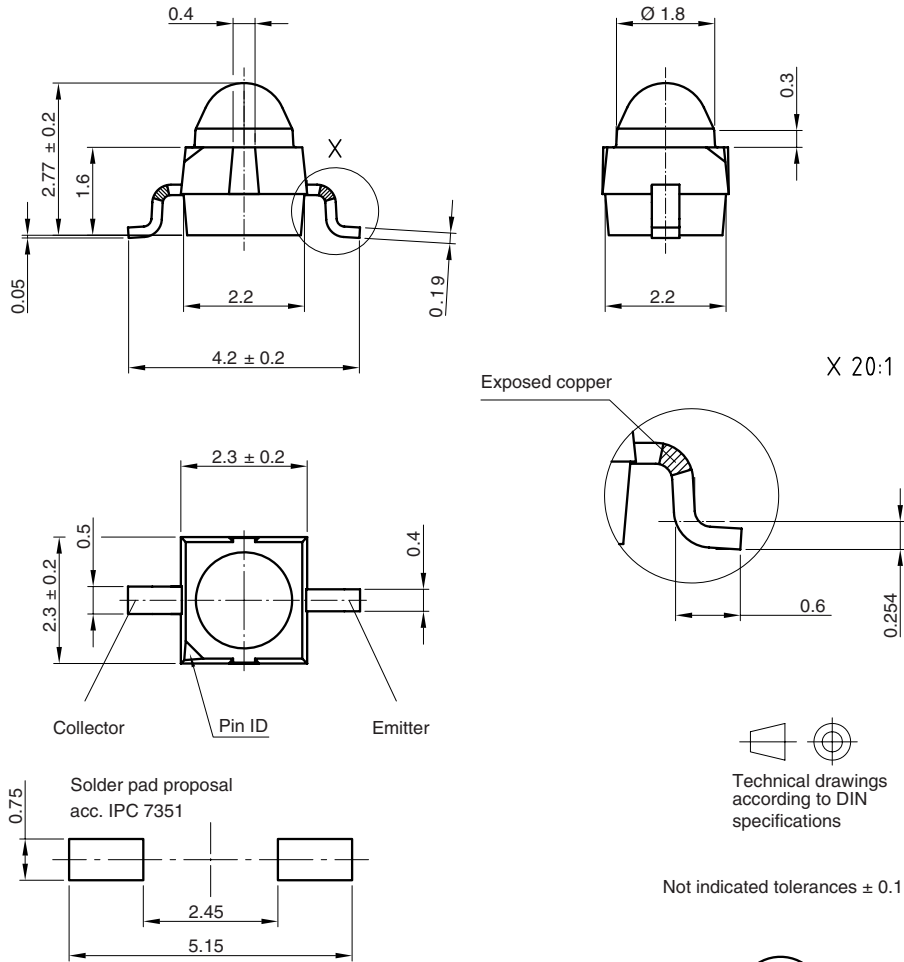


VENT2500X01, VEMT2520X01

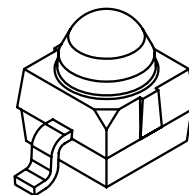
Silicon NPN Phototransistor

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PACKAGE DIMENSIONS VEMT2520X01 in millimeters



Drawing-No.: 6.544-5383.01-4
Issue: 4; 28.01.09
21569



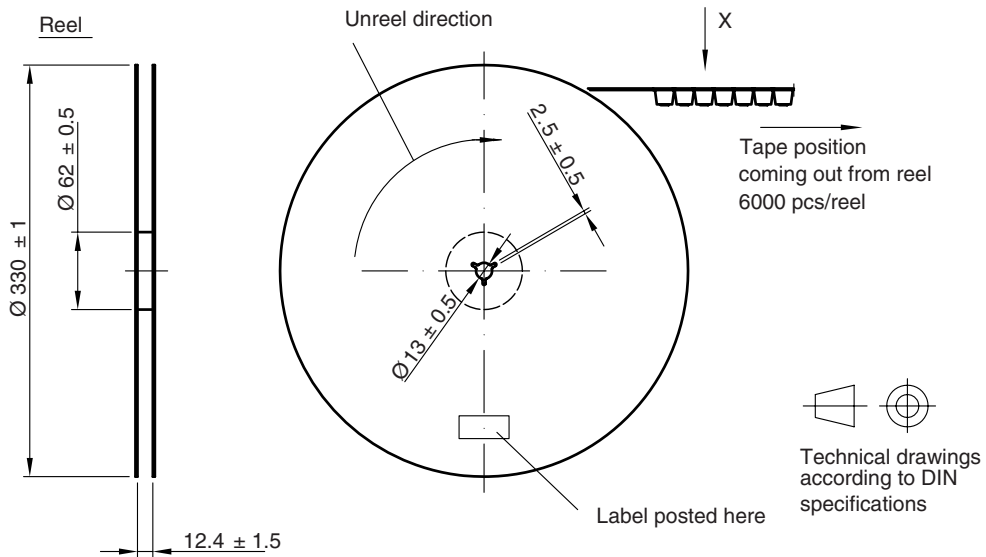
VENT2500X01, VEMT2520X01

Vishay Semiconductors

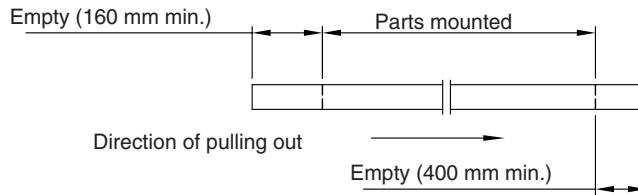
Silicon NPN Phototransistor



TAPE AND REEL DIMENSIONS VEMT2500X01 in millimeters

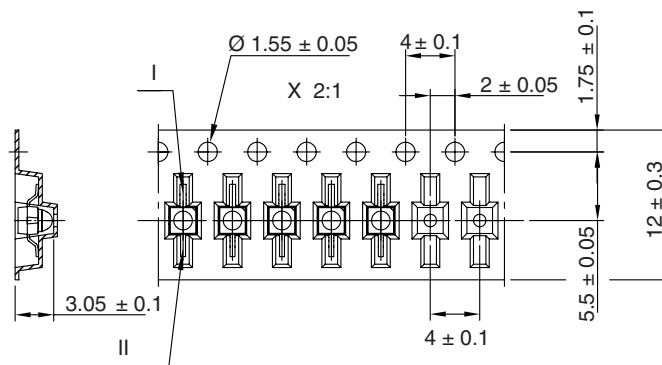


Leader and trailer tape:



Terminal position in tape

| Device | Lead I | Lead II |
|----------|-----------|---------|
| VENT2000 | Collector | Emitter |
| VEMT2500 | Collector | Emitter |
| VEMD2000 | Cathode | Anode |
| VSMB2000 | Cathode | Anode |



Drawing-No.: 9.800-5100.01-4
 Issue: X; 29.04.09
 21572

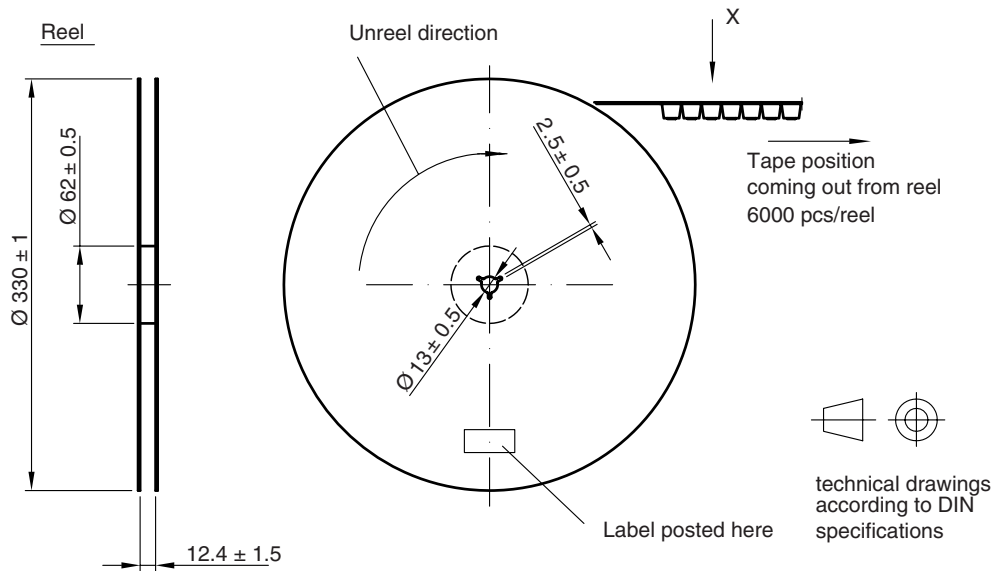


VENT2500X01, VEMT2520X01

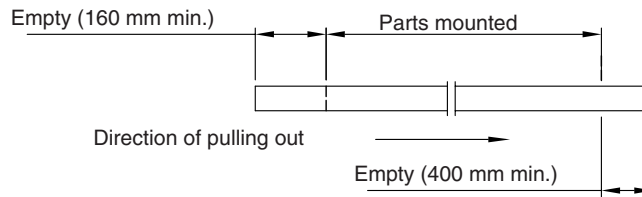
Silicon NPN Phototransistor

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TAPE AND REEL DIMENSIONS VEMT2520X01 in millimeters

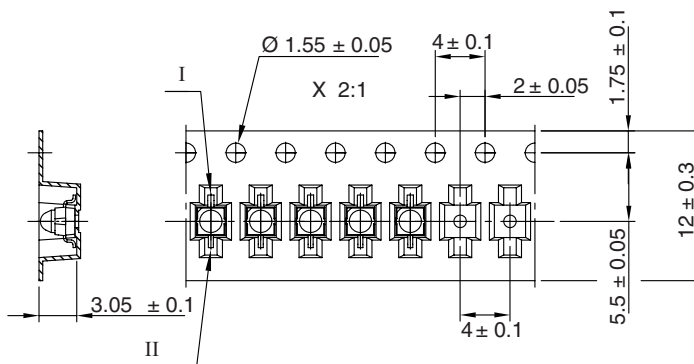


Leader and trailer tape:



Terminal position in tape

| Device | Lead I | Lead II |
|----------|-----------|---------|
| VEMT2020 | Collector | Emitter |
| VEMT2520 | Collector | Emitter |
| VSMB2020 | Cathode | Anode |
| VEMD2020 | Cathode | Anode |



Drawing-No.: 9.800-5091.01-4

Issue: X; 29.04.09

21571



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